SEMICONDUCTOR

SR60200CT,SRF60200CT,SR60200D1

SCHOTTKY BARRIER RECTIFIER

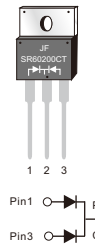
Reverse Voltage - 200 Volts

Forward Current - 60.0Amperes

RoHS COMPLIANT

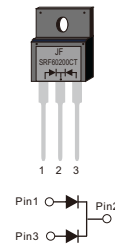
TO-220AB

SR60200CT



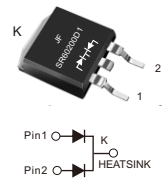
ITO-220AB

SRF60200CT



TO-263

SR60200D1



FEATURES

- Power pack
- Metal silicon junction ,majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss ,high efficiency
- High current capability ,low forward voltage drop
- High forward surge capability
- High frequency operation
- Meets MSL Level 1 , per J-STD-020,LF MAX peak of 245℃ (for TO-263 package)
- Solder bath temperature 275℃ maximum , 10s , per JESD22-B106 (for TO-220AB and ITO-220AB package)
- Component in accordance to RoHS 2011/65/EU

MECHANICAL DATA

- Case: JEDEC TO-220AB、ITO-220AB、TO-263
- Molding compound meets UL94V-0 flammability rating
- Terminals: Lead solderable per J-STD-002 and JESD22-B102
- Polarity: As marked
- Mounting Torque: 10 in-lbs maximum

TYPICAL APPLICATIONS

For use in low voltage ,high frequency inverters ,DC/DC converters,free wheeling ,and polarity protection applications

PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	2×30A
V_{RRM}	200V
I_{FSM}	400A
V_F at I_F=30.0A,Per leg	0.90V
I_R	5μA
T_J(MAX)	150℃
Package	TO-220AB,ITO-220AB, TO-263
Diode variations	Common cathode

MAXIMUM RATINGS

(Ratings at 25℃ ambient temperature unless otherwise specified)

Parameter		Symbol	Value	Unit
Maximum repetitive peak reverse voltage		V_{RRM}	200	V
Maximum average forward rectified current (see fig.1)	Per leg	$I_{F(AV)}$	30.0	A
	Total device		60.0	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method at rated TL)		I_{FSM}	400	A
Peak repetitive reverse current per diode at tp=2μs 1KHz		I_{RRM}	0.5	A
Operating junction and Storage temperature range		T_J,T_{stg}	-55 to+150	℃
Isolation voltage(ITO-220AB only)from terminals to heatsink t=1 min		V_{AC}	1500	V

RATINGS AND CHARACTERISTIC OF SR60200CT,SRF60200CT,SR60200D1

ELECTRICAL CHARACTERISTCS (T_A=25℃ Unless otherwise noted)

Parameter	Test Conditions		Symbol	Typ.	Max.	Unit
Instaneous forward voltage	Per leg I_F=30.0A	T_A=25℃	V_F 1)	0.90	0.95	V
		T_A=100℃		0.81	-	
		T_A=125℃		0.78	-	
	Per leg I_F=5.0A	T_A=25℃		0.69	-	
		T_A=100℃		0.59	-	
		T_A=125℃		0.55	-	
Reverse current	V_R=200V	T_A=25℃	I_R 2)	5	20	μA
		T_A=100℃		-	0.6	mA
		T_A=125℃		-	2.5	
Typical junction capacitance	4V,1MHz		C_J	397		pF

Notes: 1.Pulse test: 300 μs pulse width,1% duty cycle

2.Pulse test: pulse width≤40ms

THERMAL CHARACTERISTCS

Parameter	Symbol	TO-220AB	ITO-220AB	TO-263	Unit
Typical thermal resistance 3)	$R_{\theta JC}$	1.5	2.5	1.5	℃/W

3.Thermal resistance from junction to case

AVAILABALE PACK INFORMATION

Product code	Pack	Box Size L×W×H(mm)	Quantity(pcs/box)	Carton SizeL×W×H(mm)	Quantity(box/carton)
SR60200CT-TO-220AB	P/T	558×148×38	1000	565×225×170	5
SRF60200CT-ITO-220AB	P/T	558×148×38	1000	565×225×170	5
SR60200D1-TO-263	P/T	558×148×38	1000	565×225×170	5

RATINGS AND CHARACTERISTIC OF SR60200CT,SRF60200CT,SR60200D1

FIG.1-FORWARD CURRENT DERATING CURVE

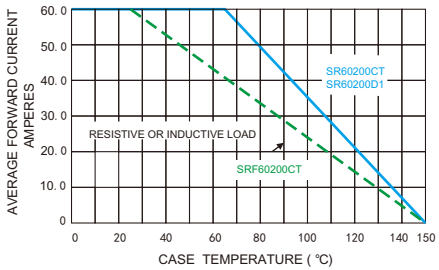


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

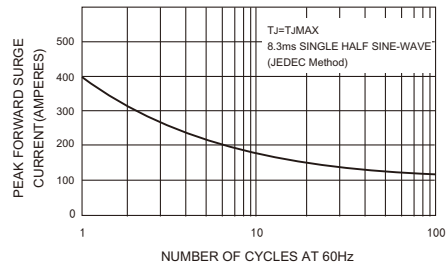


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

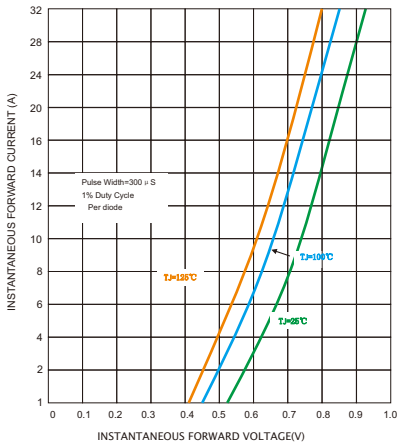


FIG.4-TYPICAL REVERSE CHARACTERISTICS

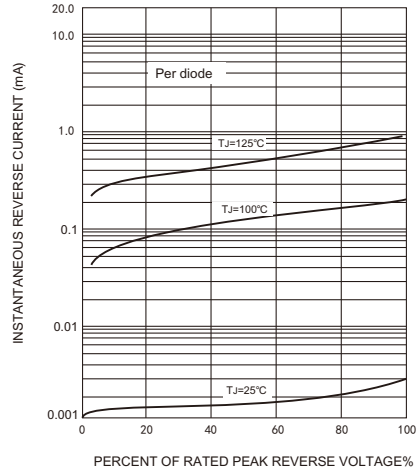
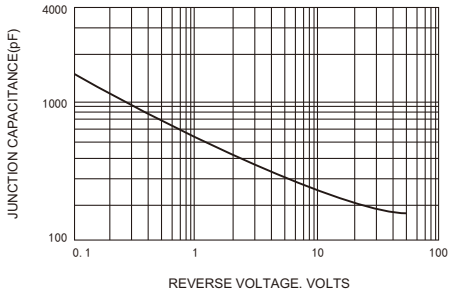
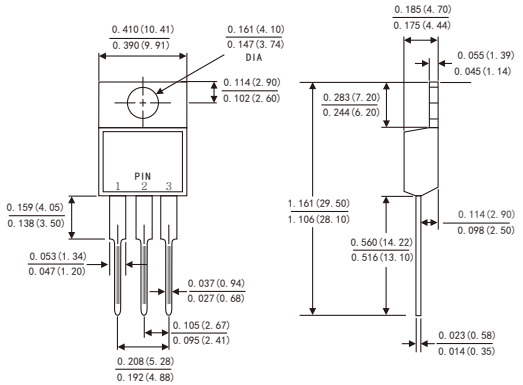


FIG.5-TYPICAL JUNCTION CAPACITANCE

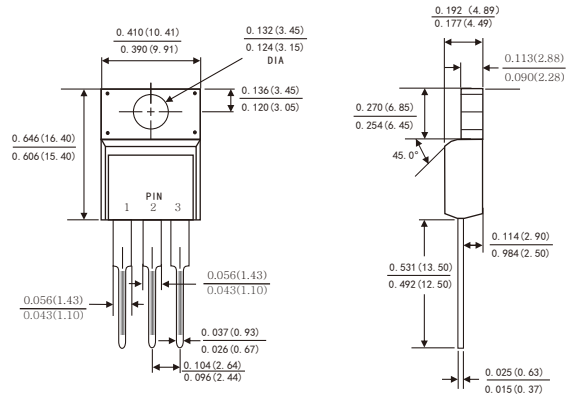


PACKAGE OUTLINE DIMENSIONS

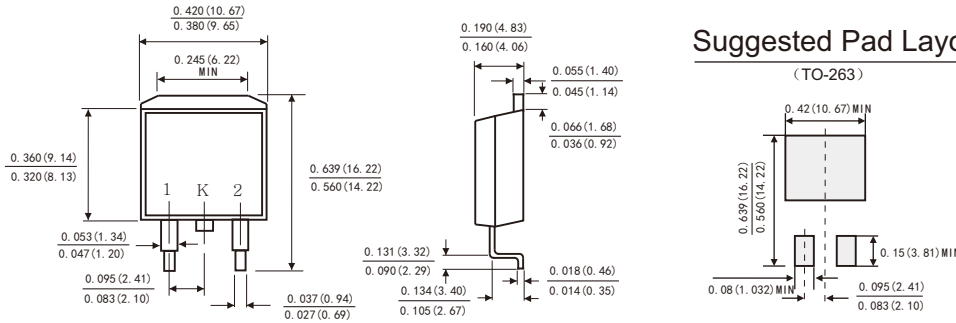
TO-220AB



ITO-220AB



TO-263



Suggested Pad Layout

（TO-263）

Dimensions in inches and (millimeters)